



THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Naoki SHIBATA

Serial No.: 09/493,819

Group Art Unit: 2698

Filed: January 28, 2000

Examiner: Douglas A. Wille

For: GROUP III NITRIDE COMPOUND SEMICONDUCTOR DEVICE

Honorable Commissioner of Patents  
Washington, D.C. 20231

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DEC 16 2002

Technology Center 2600

2814

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M. Bryson  
TECHNOLOGY CENTER 2600  
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AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated September 13, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

**Please cancel claim 4 without prejudice or disclaimer.**

**Please amend claims 3 and 6 as follows:**

3. (Twice Amended) A group III nitride compound semiconductor device of a successively laminated structure comprising:

a substrate;

a buffer layer;

a first layer formed of  $Al_xGa_bIn_{1-a-b}N$  ( $0 < a < 1$ ,  $0 < b < 1$ ,  $a+b < 1$ ); and

a second layer formed of  $In_xGa_{1-y}N$  ( $0 < Y < 1$ ),

wherein said buffer layer is disposed between and in direct contact with both said substrate and said first layer, and said first layer is disposed between and in direct contact with both said buffer layer and said second layer, and

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